

HSR101

Silicon Schottky Barrier Diode for Various detector,
High speed switching

HITACHI

ADE-208-080C (Z)
Rev. 3

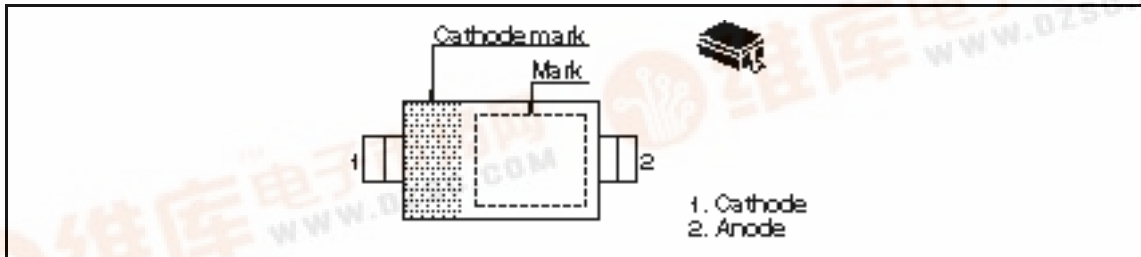
Features

- Low forward voltage, High efficiency.
- Low reverse current .
- Small Resin Package (SRP) is suitable for surface mount design.

Ordering Information

Type No.	Laser Mark	Package Code
HSR101	1	SRP

Outline



Absolute Maximum Ratings (Ta = 25°C)

Item	Symbol	Value	Unit
Reverse voltage	V_R	30	V
Forward current	I_F	35	mA
Junction temperature	T_J	100	°C
Storage temperature	T_{stg}	-55 to +100	°C

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Electrical Characteristics (Ta = 25°C)

Item	Symbol	Min	Typ	Max	Unit	Test Condition
Reverse voltage	V_R	30	—	—	V	$I_R = 10\mu\text{A}$
Reverse current	I_R	—	—	10	nA	$V_R = 10\text{V}$
Forward voltage	V_F	—	—	0.70	V	$I_F = 10\text{mA}$
Capacitance	C	—	—	1.50	pF	$V_R = 0\text{V}, f = 1\text{MHz}$
Capacitance deviation	C	—	—	0.10	pF	$V_R = 0\text{V}, f = 1\text{MHz}$
Forward voltage deviation	V_F	—	—	10	mV	$I_F = 10\text{mA}$
ESD-Capability	—	10	—	—	V	*1C = 200pF, Both forward and reverse direction 1 pulse.

- Notes: 1. Failure criterion; $I_R = 20\text{nA}$ at $V_R = 10\text{V}$.
 2. Each group shall uniform a multiple of 4 diodes.

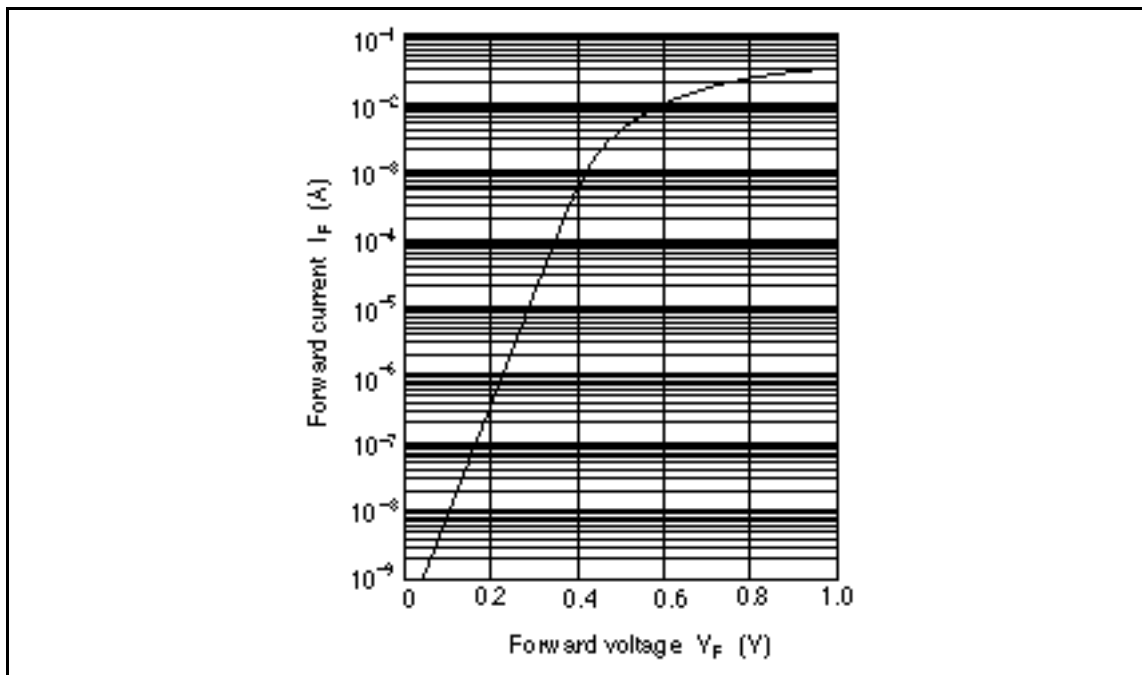


Fig.1 Forward current Vs. Forward voltage

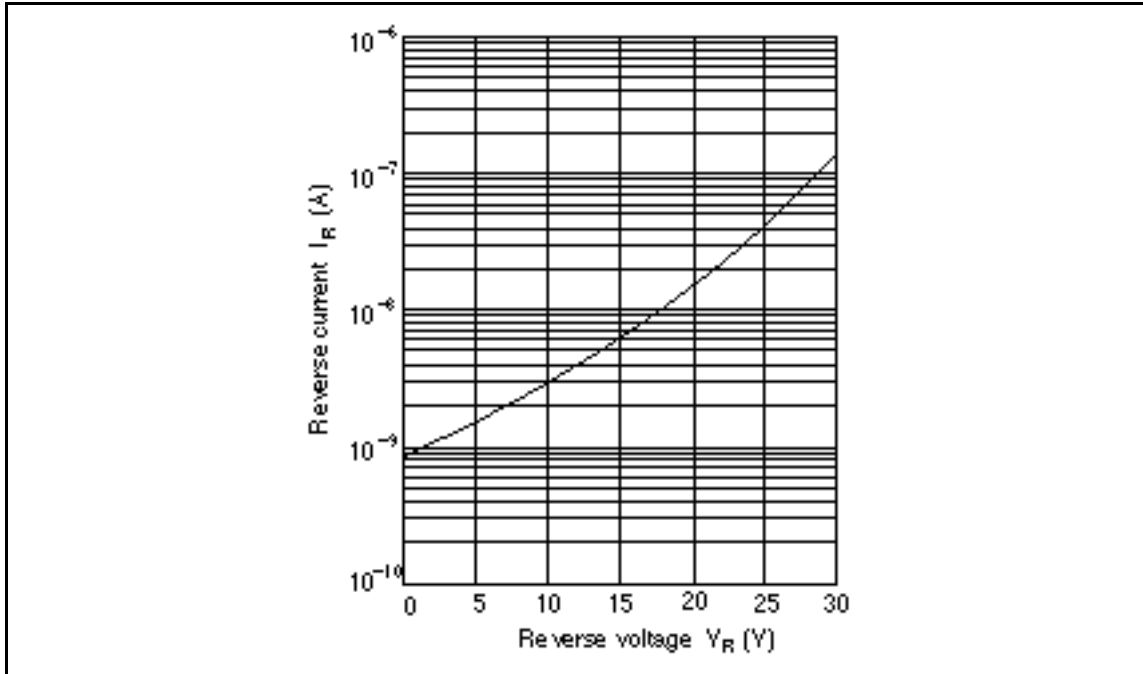


Fig.2 Reverse current Vs. Reverse voltage

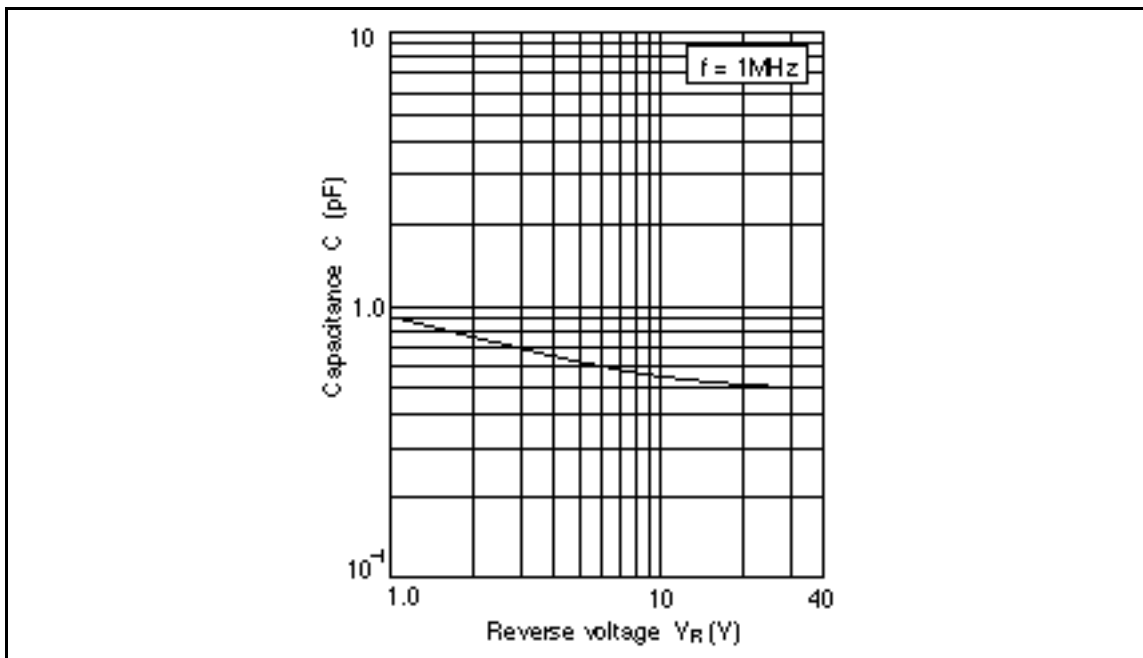


Fig.3 Capacitance Vs. Reverse voltage

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Package Dimensions

